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## Patent Abstracts of Japan

PUBLICATION NUMBER : 61027681  
PUBLICATION DATE : 07-02-86

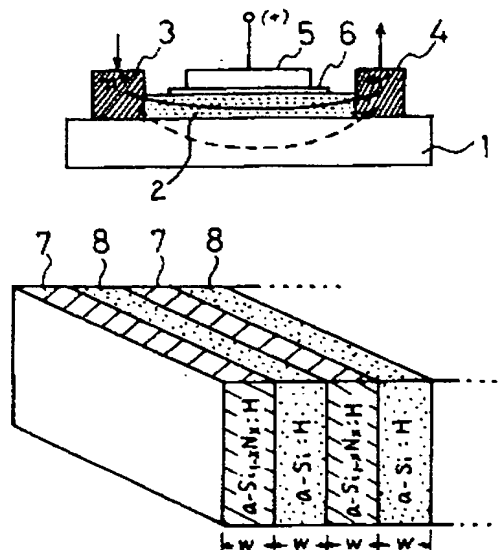
APPLICATION DATE : 17-07-84  
APPLICATION NUMBER : 59147957

APPLICANT : RES DEV CORP OF JAPAN;

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INT.CL. : H01L 29/80 H01L 29/201

TITLE : FIELD EFFECT TRANSISTOR HAVING  
CHANNEL PART OF SUPERLATTICE  
CONSTRUCTION



ABSTRACT : PURPOSE: To obtain a stable and high-speed operable field effect transistor by employing a superlattice construction formed by laminating semiconductor thin films of two kinds of semiconductors having different forbidden bands alternately in channel parts.

CONSTITUTION: A hetero junction superlattice construction formed by laminating very thin films of two kinds of semiconductors having different forbidden bands alternately is employed in channel parts. The said hetero junction superlattice construction is formed by alternately laminating super thin layers of crystals Si and  $\text{Si}_{1-x}\text{Gex}$ , non-crystalline Si and  $\text{Si}_{1-x}\text{Nx}$ , non-crystalline Si and  $\text{Si}_{1-x}\text{Cx}$  or the like. For example, a non-crystalline  $\text{a-Si}_{1-x}\text{Nx:H}$  layer 7 containing hydrogen and a non-crystalline  $\text{a-Si:H}$  layer 8 are alternately laminated on a semiconductor bulk layer 1. With the thickness of each layer W selected in the range of 30–200 $\text{\AA}$ , an active layer 2 of a heterojunction superlattice construction of which channels are formed during operation is provided and a source electrode 3, a drain electrode 4, a gate electrode 5 and a gate insulating film 6 of  $\text{SiO}_2$ ,  $\text{Si}_3\text{N}_4$  or the like are provided too, thereby to produce a thin film field effect transistor.

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